IGBT − Field Stop, Trench

75 A, 950 V

Product Preview

FGY75T95LQDT

Trench Field Stop 4th generation Low Vcesat IGBT co−packaged with full current rated diode.

Features

- Maximum Junction Temperature : T_J = 175°C
- Positive Temperature Co−efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(Sat)}$ = 1.31 V (Typ.) @ I_C = 75 A
- Fast Switching
- Tighten Parameter Distribution
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Solar Inverter

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector to Emitter Voltage	V_{CES}	950	V
Gate to Emitter Voltage Transient Gate to Emitter Voltage	V_{GES}	±20 ±30	V
Collector Current @T_C = 25°C @T_C = 100°C	I_C	150 75	A
Pulsed Collector Current (Note 1)	I_{LM}	225	A
Pulsed Collector Current (Note 2)	I_{CM}	225	A
Diode Forward Current @T_C = 25°C @T_C = 100°C	I_F	150 75	A
Pulsed Diode Forward Current (Note 2)	I_{FM}	225	A
Maximum Power Dissipation @T_C = 25°C @T_C = 100°C	P_D	453 226	W
Operating Junction / Storage Temperature Range	T_J, T_{STG}	−55 to +175	°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. VCC = 700 V, VGE = 15 V, IC = 225 A, RG = 26 Ω, Inductive Load, 100% Tested
2. Pulse width limited by max Junction temperature. Defined by design. Not subject to production test

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

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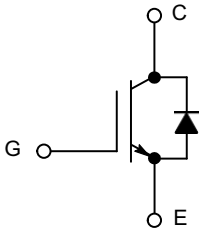
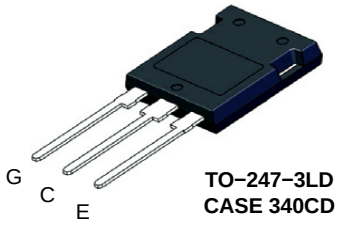
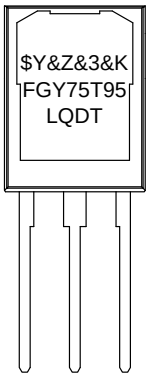
75 A, 950 V
V_{CESat} = 1.31 V (Typ.)





TO−247−3LD
CASE 340CD

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= 2−Digit Lot Traceability Code
FGY75T95LQDT	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FGY75T95LQDT	FGY75T95LQDT	TO−247−3LD (Pb-Free)	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case, for IGBT	$R_{\theta JC}$	0.33	°C/W
Thermal resistance junction−to−case, for Diode	$R_{\theta JC}$	0.23	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 1 mA	BV_{CES}	950			V
Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 1 mA	$\frac{\Delta BV_{CES}}{\Delta T_J}$		0.96		V/°C
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 950 V	I_{CES}			250	μA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V , V_{CE} = 0 V	I_{GES}			±400	nA
ON CHARACTERISTICS						
Gate−emitter threshold voltage	V_{GE} = V_{CE}, I_C = 75 mA	$V_{GE(th)}$	3.4	4.57	6.4	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 75 A V_{GE} = 15 V, I_C = 75 A, T_J = 175°C	$V_{CE(sat)}$		1.31 1.52	1.69	V
DYNAMIC CHARACTERISTICS						
Input capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	Cies		15400		pF
Output capacitance		Coes		266		
Reverse transfer capacitance		Cres		85.3		
Gate charge total	V_{CE} = 600 V, I_C = 75 V, V_{GE} = 15 V	Q_g		663.3		nC
Gate to emitter charge		Qge		76.1		
Gate to collector charge		Qgc		218.6		
SWITCHING CHARACTERISTICS, INDUCTIVE LOAD						
Turn−on delay time	T_J = 25°C V_{CC} = 600 V, I_C = 37.5 A Rg = 4.7 Ω V_{GE} = 15 V Inductive Load	td(on)		52.0		ns
Rise time		t_r		24.0		
Turn−off delay time		td(off)		496.0		
Fall time		t_f		108.0		
Turn−on switching loss		Eon		2.0		mJ
Turn−off switching loss		Eoff		1.8		
Total switching loss		Ets		3.7		

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Turn−on delay time	T_J = 25°C V_{CC} = 600 V, I_C = 75 A Rg = 4.7 Ω V_{GE} = 15 V Inductive Load	td(on)		52.0		ns
Rise time		t_r		52.0		
Turn−off delay time		td(off)		476.0		
Fall time		t_f		76.0		
Turn−on switching loss		Eon		4.8		mJ
Turn−off switching loss		Eoff		3.3		
Total switching loss		Ets		8.1		
Turn−on delay time	T_J = 175°C V_{CC} = 600 V, I_C = 37.5 A Rg = 4.7 Ω V_{GE} = 15 V Inductive Load	td(on)		44.0		ns
Rise time		t_r		30.0		
Turn−off delay time		td(off)		580.0		
Fall time		t_f		144.0		
Turn−on switching loss		Eon		3.8		mJ
Turn−off switching loss		Eoff		2.7		
Total switching loss		Ets		6.5		
Turn−on delay time	T_J = 175°C V_{CC} = 600 V, I_C = 75 A Rg = 4.7 Ω V_{GE} = 15 V Inductive Load	td(on)		48.0		ns
Rise time		t_r		54.0		
Turn−off delay time		td(off)		548.0		
Fall time		t_f		118.0		
Turn−on switching loss		Eon		7.6		mJ
Turn−off switching loss		Eoff		5.1		
Total switching loss		Ets		12.7		
DIODE CHARACTERISTICS						
Forward voltage	I_F = 75 A I_F = 75 A, T_J = 175°C	V_F		2.03 1.76	2.51	V
Reverse Recovery Energy	T_J = 25°C V_R = 600 V, I_F = 37.5 A dI_F/dt = 1000 A/μs	E_{rec}		314		uJ
Reverse Recovery Time		t_{rr}		105		ns
Reverse Recovery Charge		Q_{rr}		1635		nC
Reverse Recovery Energy	T_J = 25°C V_R = 600 V, I_F = 75 A dI_F/dt = 1000 A/μs	E_{rec}		2390		uJ
Reverse Recovery Time		t_{rr}		259		ns
Reverse Recovery Charge		Q_{rr}		7515		nC
Reverse Recovery Energy	T_J = 175°C V_R = 600 V, I_F = 37.5 A dI_F/dt = 1000 A/μs	E_{rec}		454		uJ
Reverse Recovery Time		t_{rr}		148		ns
Reverse Recovery Charge		Q_{rr}		2436		nC

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Reverse Recovery Energy	T_J = 175°C V_R = 600 V, I_F = 75 A dI_F/dt = 1000 A/μs	E_{rec}		2790		uJ
Reverse Recovery Time		t_{rr}		294		ns
Reverse Recovery Charge		Q_{rr}		9175		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

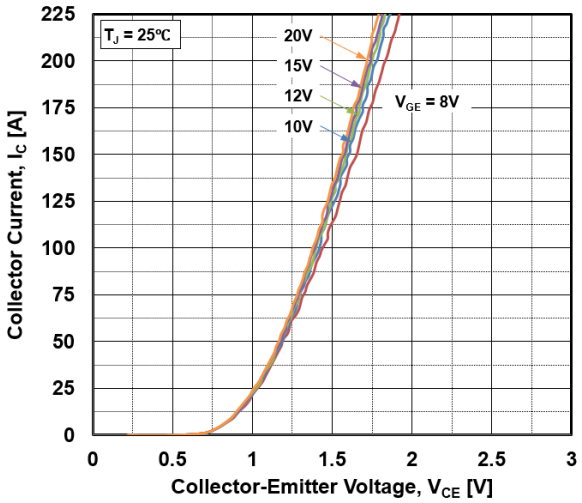


Figure 1. Typical Output Characteristics (T_J = 25°C)

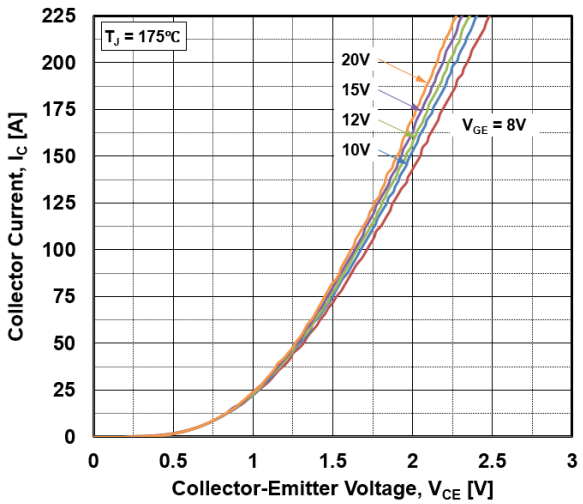


Figure 2. Typical Output Characteristics (T_J = 175°C)

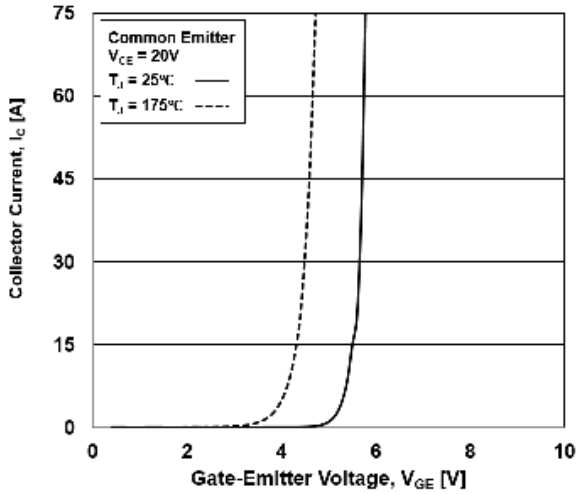


Figure 3. Transfer Characteristics

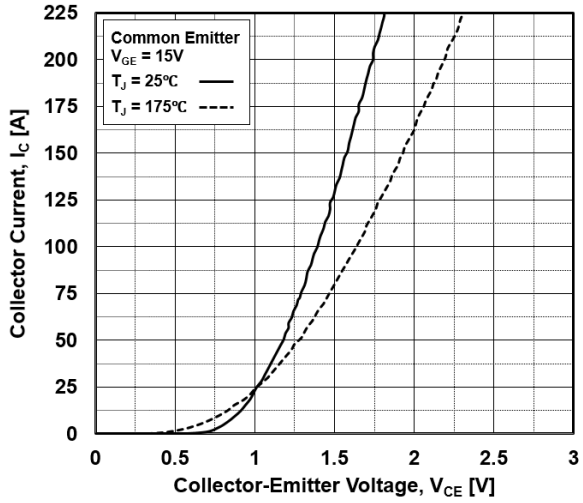


Figure 4. Typical Saturation Voltage Characteristics

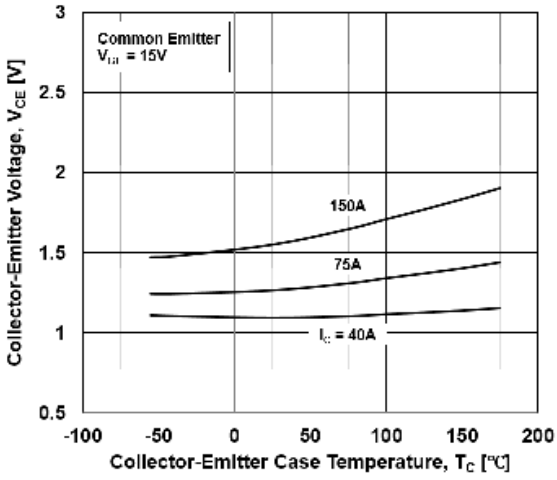


Figure 5. Saturation Voltage vs Case Temperature at Variant Current Level

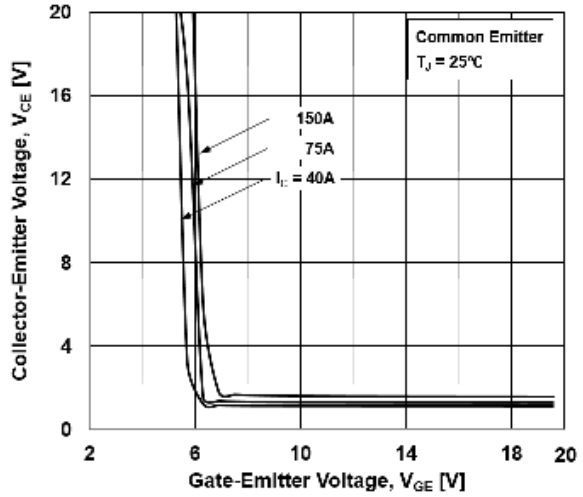


Figure 6. Saturation Voltage vs. V_{GE} (T_J = 25°C)

TYPICAL CHARACTERISTICS

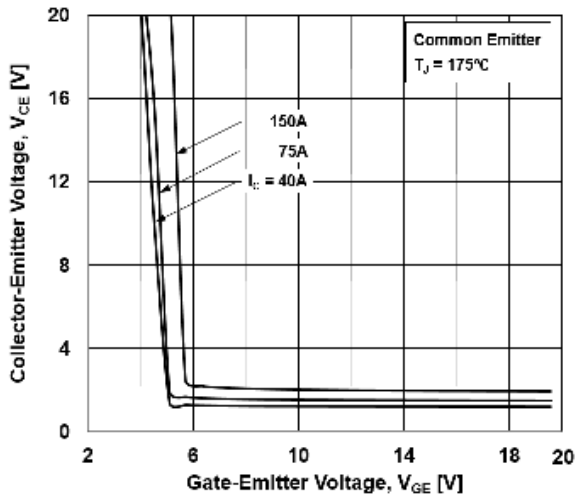


Figure 7. Saturation Voltage vs. V_{GE} (T_J = 175°C)

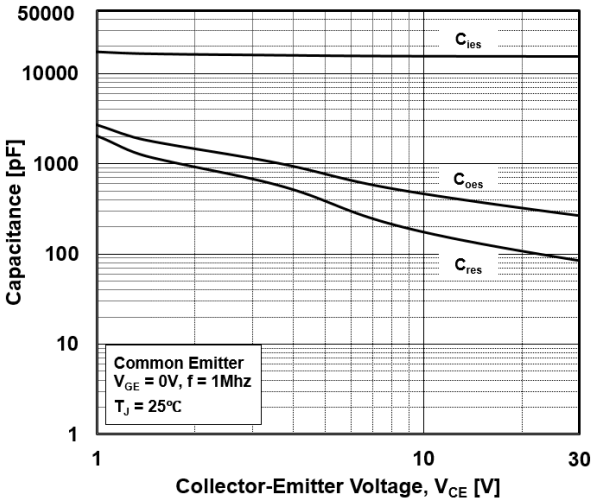


Figure 8. Capacitance Characteristics

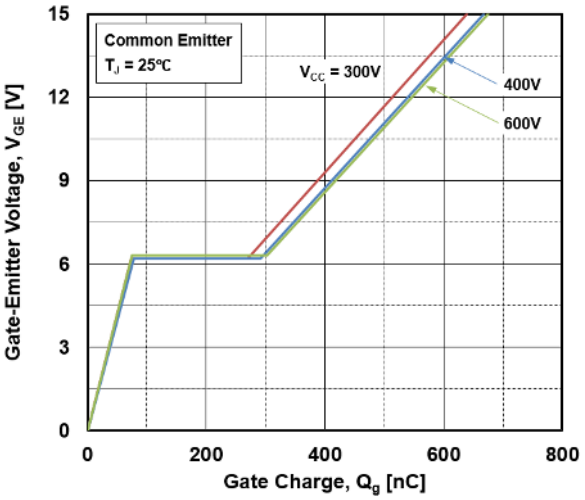


Figure 9. Gate Charge Characteristics (T_J = 25°C)

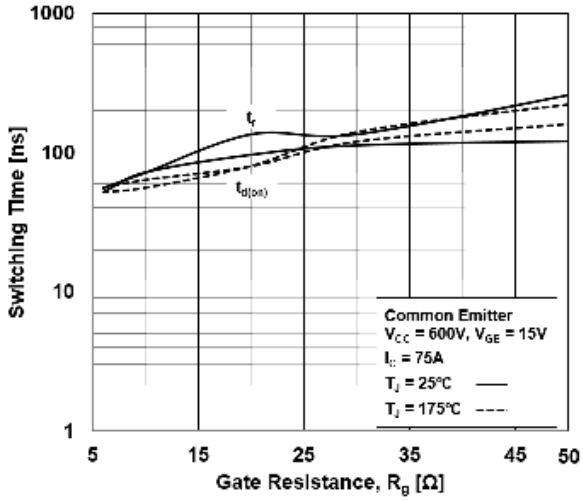


Figure 10. Turn−on Characteristics vs. Gate Resistance

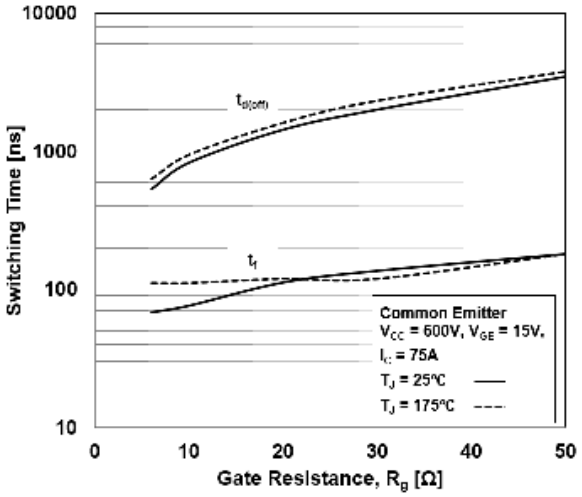


Figure 11. Turn−off Characteristics vs. Gate Resistance

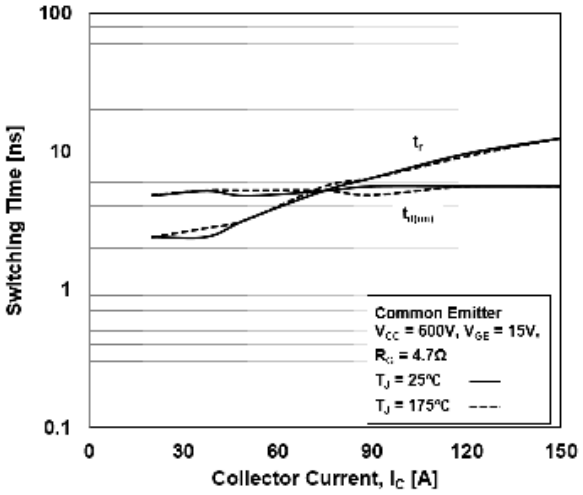


Figure 12. Turn−on Characteristics vs. Collector Current

TYPICAL CHARACTERISTICS

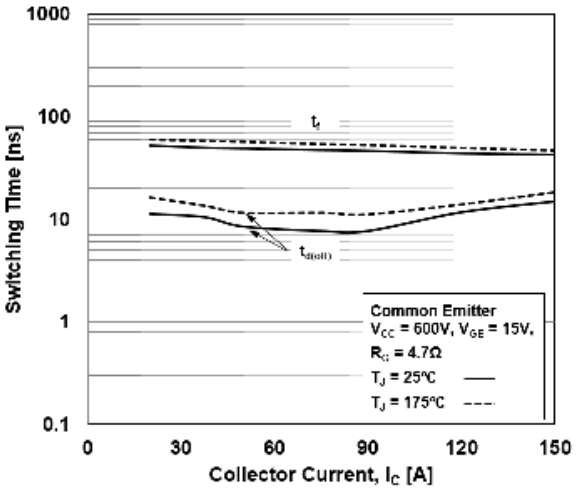


Figure 13. Turn−off Characteristics vs. Collector Current

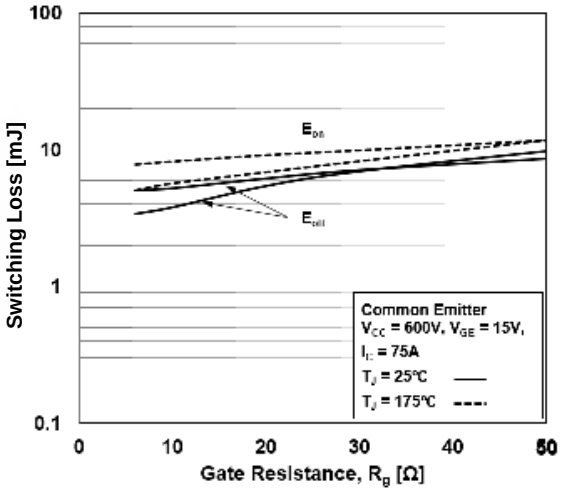


Figure 14. Switching Loss vs. Gate Resistance

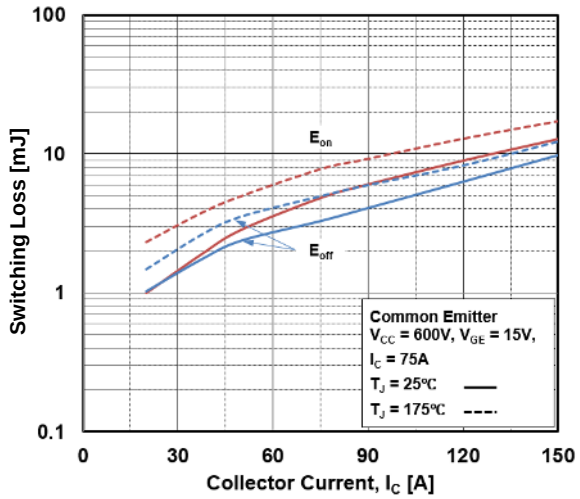


Figure 15. Switching Loss vs. Collector Current

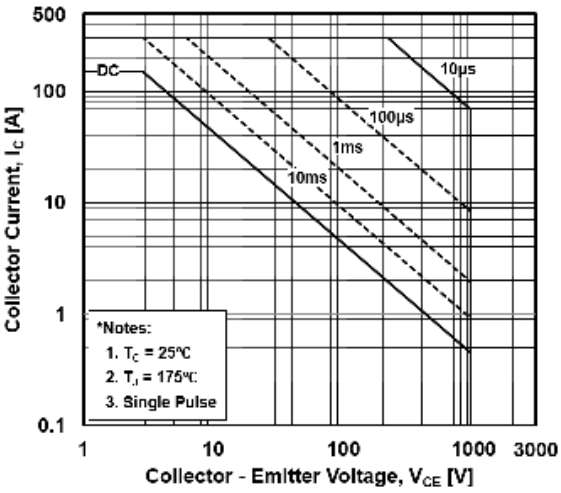


Figure 16. SOA Characteristics (FBSOA)

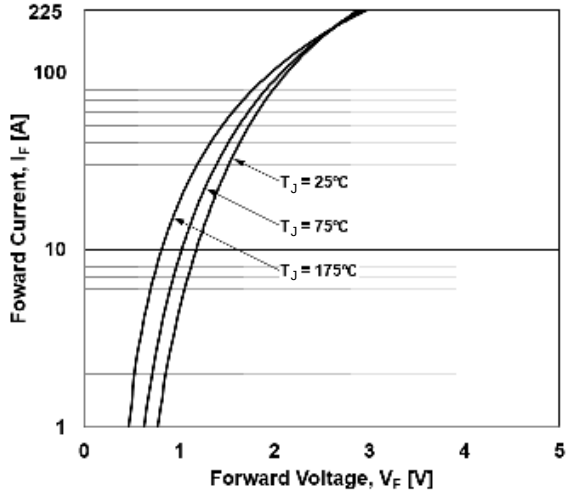


Figure 17. (Diode) Forward Characteristics vs (Normal I−V)

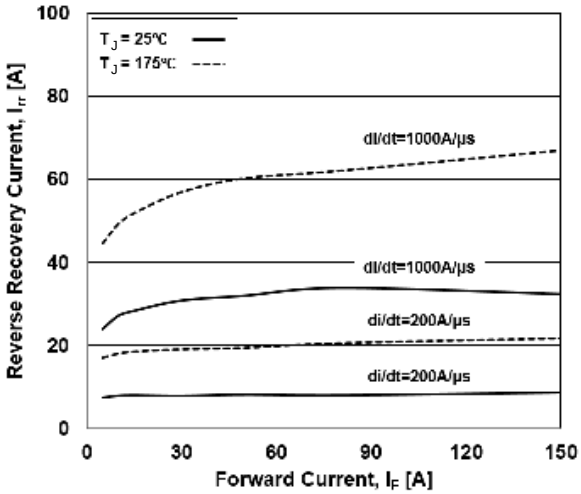


Figure 18. (Diode) Reverse Recovery Current

TYPICAL CHARACTERISTICS

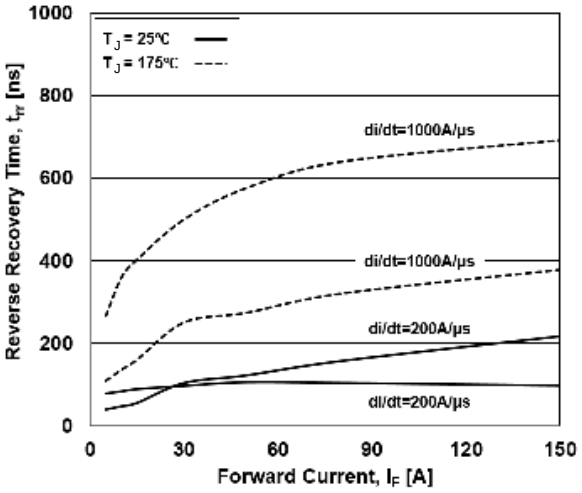


Figure 19. (Diode) Reverse Recovery Time

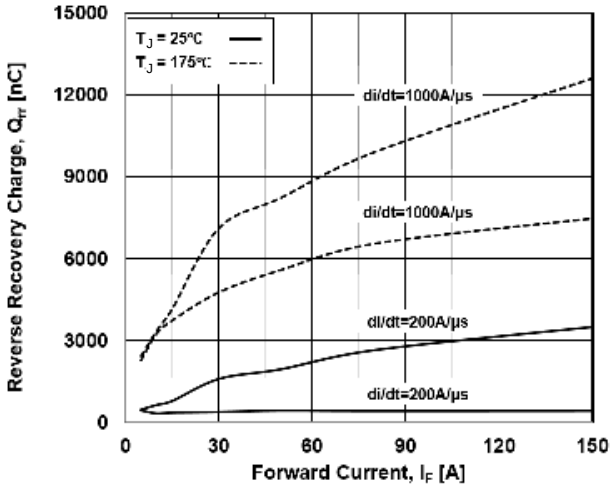


Figure 20. (Diode) Stored Charge

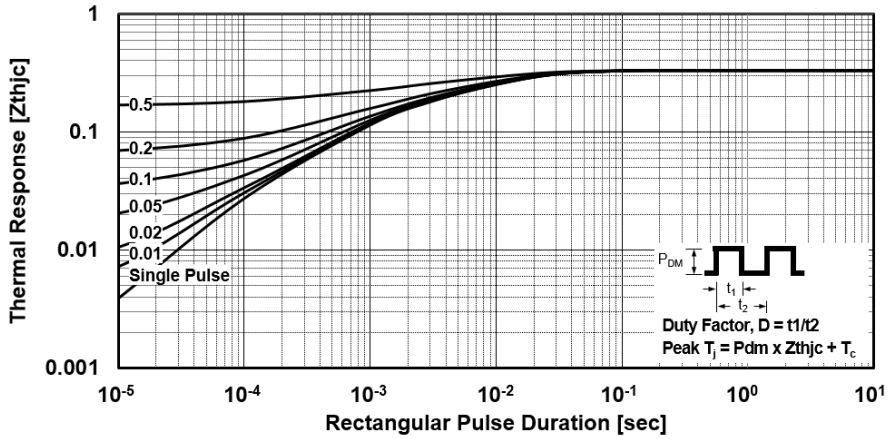


Figure 21. Transient Thermal Impedance of IGBT

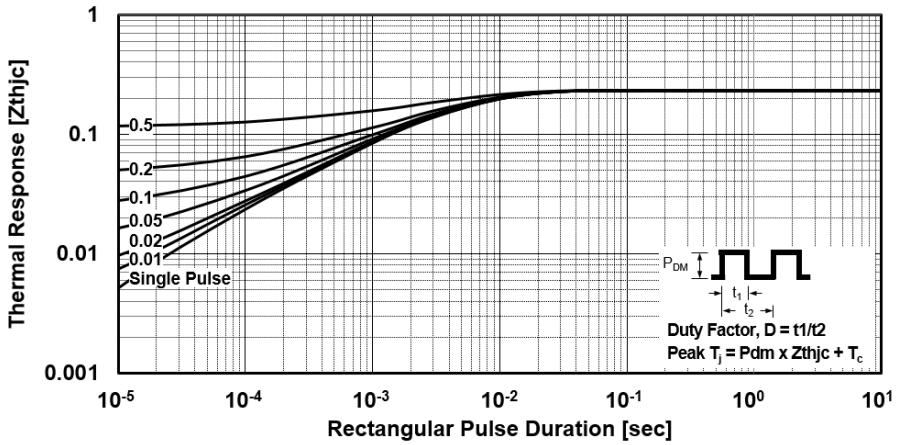
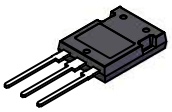


Figure 22. Transient Thermal Impedance of Diode

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

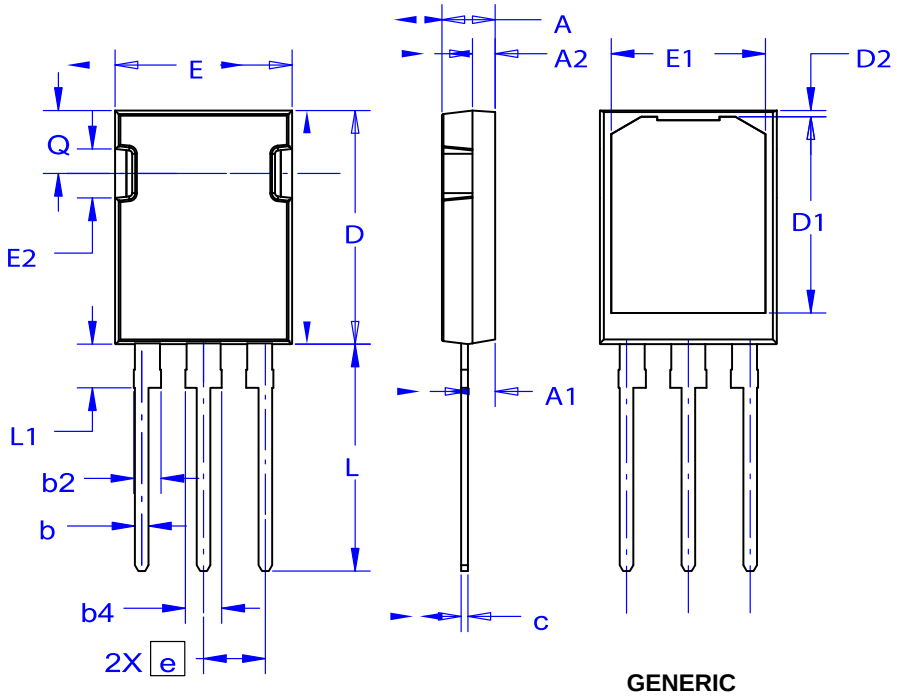


TO−247−3LD
CASE 340CD
ISSUE A

DATE 18 SEP 2018

NOTES:

A. THIS PACKAGE DOES NOT CONFORM TO ANY STANDARDS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.12	4.32	4.52
e	~	5.45	~
L	19.90	20.00	20.10
L1	3.69	3.81	3.93
Q	5.34	5.46	5.58
b	1.10	1.20	1.30
b2	2.10	2.24	2.39
b4	2.87	3.04	3.20
c	0.51	0.61	0.71
D1	16.63	16.83	17.03
D2	0.51	0.93	1.35
E1	13.40	13.60	13.80

GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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